



The ZM085N03K combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	19	A
	$I_{D@TC=75}$	14.4	A
	$I_{D@TC=100}$	12	A
Pulsed Drain Current	I_{DM}	45	A
Total Power Dissipation	$P_D@TC=25$	3.1	W
Total Power Dissipation	$P_D@TA=25$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	43	mJ
Avalanche Current@L=0.1mH	I_{AS}	28	A





Fig.1 Power Dissipation

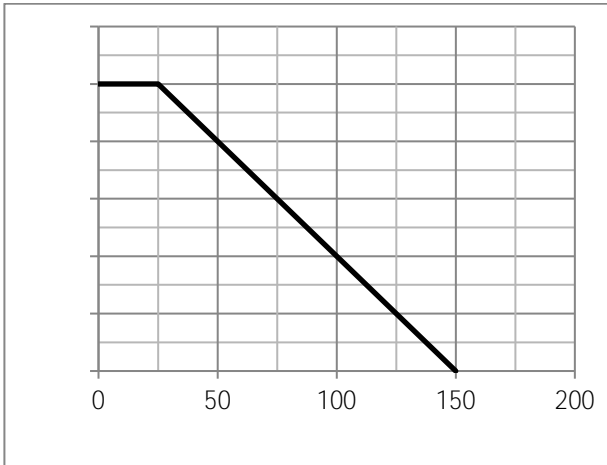


Fig.2 Typical output Characteristics

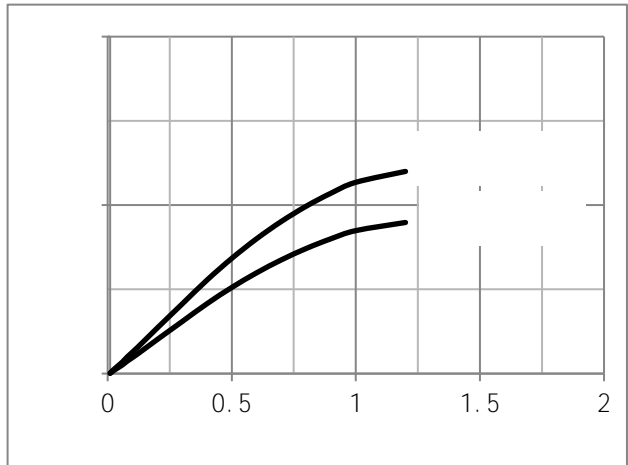


Fig.3 Threshold Voltage V.S Junction Temperature

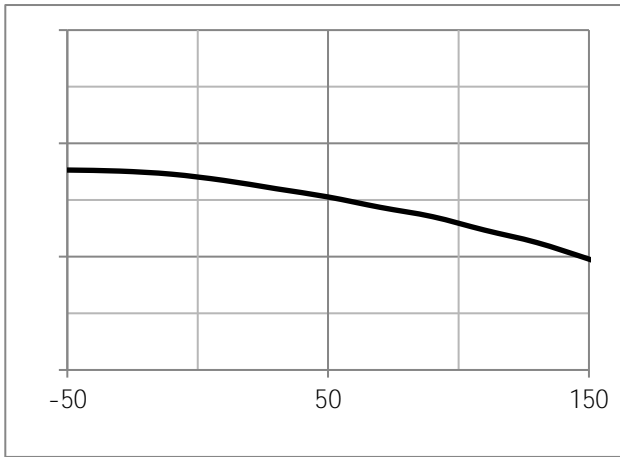


Fig.4 Resistance V.S Drain Current

